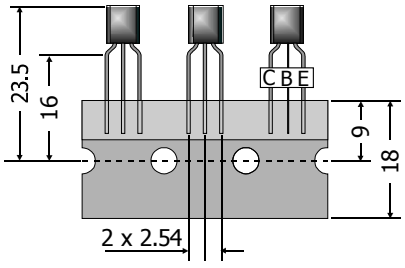
Diotec Semiconductor

2N4401

NPN **General Purpose Si-Epitaxial Planar Transistors**
Si-Epitaxial Planar-Transistoren für universellen Einsatz **NPN**

Version 2006-09-12



Dimensions - Maße [mm]

Power dissipation Verlustleistung	625 mW
Plastic case Kunststoffgehäuse	TO-92 (10D3)
Weight approx. – Gewicht ca.	0.18 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging taped in ammo pack Standard Lieferform gegurtet in Ammo-Pack	

Maximum ratings (T_A = 25°C) Grenzwerte (T_A = 25°C)

			2N4401
Collector-Emitter-volt. – Kollektor-Emitter-Spannung	B open	V_{CEO}	40 V
Collector-Base-voltage – Kollektor-Basis-Spannung	E open	V_{CBO}	60 V
Emitter-Base-voltage – Emitter-Basis-Spannung	C open	V_{EBO}	6 V
Power dissipation – Verlustleistung		P_{tot}	250 mW [1])
Collector current – Kollektorstrom (dc)		I_C	600 mA
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_S	-55...+150°C -55...+150°C

Characteristics (T_j = 25°C) Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis [2])				
I_C = 0.1 mA, V_{CE} = 1 V	h_{FE}	20	–	–
I_C = 1 mA, V_{CE} = 1 V	h_{FE}	40	–	–
I_C = 10 mA, V_{CE} = 1 V	h_{FE}	80	–	–
I_C = 150 mA, V_{CE} = 1 V	h_{FE}	100	–	300
I_C = 500 mA, V_{CE} = 2 V	h_{FE}	40	–	–
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungsspg. [2])				
I_C = 150 mA, I_B = 15 mA	V_{CEsat}	–	–	0.40 V
I_C = 500 mA, I_B = 50 mA	V_{CEsat}	–	–	0.75 V
Base-Emitter saturation voltage – Basis-Emitter-Sättigungsspannung [2])				
I_C = 150 mA, I_B = 15 mA	V_{BEsat}	0.75 V	–	0.95 V
I_C = 500 mA, I_B = 50 mA	V_{BEsat}	–	–	1.2 V

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss
2 Tested with pulses t_p = 300 µs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%

Characteristics (T_j = 25°C) **Kennwerte (T_j = 25°C)**

			Min.	Typ.	Max.
Collector-Base cutoff current – Kollektor-Basis-Reststrom V_{CE} = 35 V, V_{EB} = 0,4 V		I_{CBV}	–	–	100 nA
Emitter-Base cutoff current – Emitter-Basis-Reststrom V_{CE} = 35 V, V_{EB} = 0,4 V		I_{EBV}	–	–-	100 nA
Gain-Bandwidth Product – Transitfrequenz I_C = 20 mA, V_{CE} = 10 V, f = 100 MHz		f_T	250 MHz	–	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität V_{CB} = 5 V, I_E = i_e = 0, f = 1 MHz		C_{CBO}	–	–	6.5 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität V_{EB} = 0.5 V, I_C = i_c = 0, f = 1 MHz		C_{EBO}	–	–	30 pf
Switching times – Schaltzeiten (between 10% and 90% levels)					
delay time	V_{CC} = 30 V, V_{EB} = 2 V I_C = 150 mA, I_{B1} = 15 mA	t_d	–	–	15 ns
rise time		t_r	–	–	20 ns
storage time	V_{CC} = 30 V, I_C = 150 mA, I_{B1} = I_{B2} = 15 mA	t_s	–	–	225 ns
fall time		t_f	–	–	30 ns
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft		R_{thA}	< 200 K/W [1])		
Recommended complementary PNP transistors Empfohlene komplementäre PNP-Transistoren			2N4403		

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss

